

Highly insulated module with Trench/Fieldstop IGBT3 and emitter controlled 3 diode**Features**

- Electrical features
 - $V_{CES} = 6500 \text{ V}$
 - $I_{C\text{nom}} = 600 \text{ A} / I_{CRM} = 1200 \text{ A}$
 - Low $V_{CE,sat}$
- Mechanical features
 - ALSiC base plate for increased thermal cycling capability
 - Extended storage temperature down to $T_{stg} = -55 \text{ }^\circ\text{C}$
 - High creepage and clearance distances
 - Package with CTI > 600
 - Package with enhanced insulation of 10.4 kV AC 60 s

**Potential applications**

- Medium-voltage converters
- Traction drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

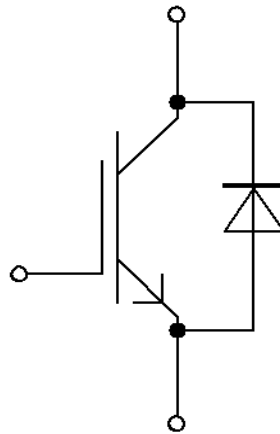
Description

Table of contents

	Description	1
	Features	1
	Potential applications	1
	Product validation	1
	Table of contents	2
1	Package	3
2	IGBT, Inverter	3
3	Diode, Inverter	5
4	Characteristics diagrams	7
5	Circuit diagram	10
6	Package outlines	11
7	Module label code	12
	Revision history	13
	Disclaimer	14

1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 60 \text{ s}$	10.4	kV
Partial discharge extinction voltage	V_{isol}	RMS, $f = 50 \text{ Hz}$, Q_{PD} typ. 10 pC	5.1	kV
DC stability	$V_{CE(D)}$	$T_{vj}=25^{\circ}\text{C}$, 100 Fit	3800	V
Material of module baseplate			AlSiC	
Internal isolation		basic insulation (class 1, IEC 61140)	AlN	
Creepage distance	d_{Creep}	terminal to heatsink	64.0	mm
Creepage distance	d_{Creep}	terminal to terminal	56.0	mm
Clearance	d_{Clear}	terminal to heatsink	40.0	mm
Clearance	d_{Clear}	terminal to terminal	26.0	mm
Comparative tracking index	CTI		>600	

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Stray inductance module	L_{sCE}			18		nH	
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_C=25^{\circ}\text{C}$, per switch		0.12		mΩ	
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C=25^{\circ}\text{C}$, per switch		0.12		mΩ	
Storage temperature	T_{stg}		-55		125	°C	
Mounting torque for module mounting	M	- Mounting according to valid application note	M6, Screw	4.25		5.75	Nm
Terminal connection torque	M	- Mounting according to valid application note	M4, Screw	1.8		2.1	Nm
			M8, Screw	8		10	
Weight	G			1400		g	

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Collector-emitter voltage	V_{CES}		$T_{vj} = -50^{\circ}\text{C}$	5900	V
			$T_{vj} = 25^{\circ}\text{C}$	6500	
			$T_{vj} = 125^{\circ}\text{C}$	6500	

(table continues...)

Table 3 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Continuous DC collector current	I_{CDC}	$T_{vj\ max} = 150\ ^\circ C$ $T_C = 80\ ^\circ C$	600	A
Repetitive peak collector current	I_{CRM}	$t_p = 1\ ms$	1200	A
Gate-emitter peak voltage	V_{GES}		± 20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 600\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$	3.00	3.40	V
			$T_{vj} = 125\ ^\circ C$	3.70	4.30	
Gate threshold voltage	V_{GEth}	$I_C = 105\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$	5.40	6	6.60	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CE} = 3600\ V$		25		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$		0.75		Ω
Input capacitance	C_{ies}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		160		nF
Reverse transfer capacitance	C_{res}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		2.5		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 6500\ V, V_{GE} = 0\ V$ $T_{vj} = 25\ ^\circ C$			5	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$			400	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 600\ A, V_{CE} = 3600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 1.3\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.640		μs
			$T_{vj} = 125\ ^\circ C$	0.650		
Rise time (inductive load)	t_r	$I_C = 600\ A, V_{CE} = 3600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 1.3\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.180		μs
			$T_{vj} = 125\ ^\circ C$	0.200		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 600\ A, V_{CE} = 3600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 8.2\ \Omega$	$T_{vj} = 25\ ^\circ C$	7.300		μs
			$T_{vj} = 125\ ^\circ C$	7.600		
Fall time (inductive load)	t_f	$I_C = 600\ A, V_{CE} = 3600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 8.2\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.400		μs
			$T_{vj} = 125\ ^\circ C$	0.500		
Turn-on time (resistive load)	t_{on_R}	$I_C = 500\ A, V_{CE} = 2000\ V, V_{GE} = \pm 15\ V, R_{Gon} = 1.3\ \Omega$	1.29			μs
Turn-on energy loss per pulse	E_{on}	$I_C = 600\ A, V_{CE} = 3600\ V, L_\sigma = 280\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 1.3\ \Omega, di/dt = 2400\ A/\mu s (T_{vj} = 125\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	3400		mJ
			$T_{vj} = 125\ ^\circ C$	5200		
Turn-off energy loss per pulse	E_{off}	$I_C = 600\ A, V_{CE} = 3600\ V, L_\sigma = 280\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 8.2\ \Omega$	$T_{vj} = 25\ ^\circ C$	2900		mJ
			$T_{vj} = 125\ ^\circ C$	3400		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
SC data	I_{SC}	$V_{GE} \leq 15 \text{ V}$, $V_{CC} = 4500 \text{ V}$, $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$t_P \leq 10 \mu\text{s}$, $T_{vj} \leq 125 \text{ }^\circ\text{C}$		3600		A
Thermal resistance, junction to case	R_{thJC}	per IGBT				10.2	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1 \text{ W}/(\text{m}^2\text{K})$			9.20		K/kW
Temperature under switching conditions	T_{vjop}			-50		125	$^\circ\text{C}$

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = -50 \text{ }^\circ\text{C}$	5900	V
			$T_{vj} = 25 \text{ }^\circ\text{C}$	6500	
			$T_{vj} = 125 \text{ }^\circ\text{C}$	6500	
Continuous DC forward current	I_F		600	A	
Repetitive peak forward current	I_{FRM}	$t_P = 1 \text{ ms}$	1200	A	
I^2t - value	I^2t	$t_P = 10 \text{ ms}$, $V_R = 0 \text{ V}$	$T_{vj} = 125 \text{ }^\circ\text{C}$	300	kA^2s
Maximum power dissipation	P_{RQM}	$T_{vj} = 125 \text{ }^\circ\text{C}$	2400	kW	
Minimum turn-on time	t_{onmin}		10	μs	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Forward voltage	V_F	$I_F = 600 \text{ A}$, $V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		3.00	3.50	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$		2.95	3.60	
Peak reverse recovery current	I_{RM}	$V_R = 3600 \text{ V}$, $I_F = 600 \text{ A}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 2400 \text{ A}/\mu\text{s}$ ($T_{vj} = 125 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$		900		A
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1000		
Recovered charge	Q_r	$V_R = 3600 \text{ V}$, $I_F = 600 \text{ A}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 2400 \text{ A}/\mu\text{s}$ ($T_{vj} = 125 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$		700		μC
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1300		

(table continues...)

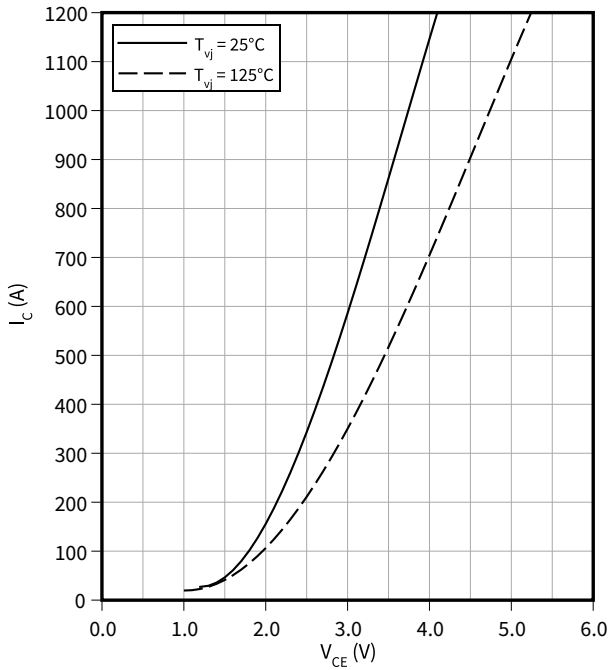
Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Reverse recovery energy	E_{rec}	$V_R = 3600\text{ V}$, $I_F = 600\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt =$ $2400\text{ A}/\mu\text{s}$ ($T_{vj} = 125\text{ }^\circ\text{C}$)	$T_{vj} = 25\text{ }^\circ\text{C}$	1100		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	2400		
Thermal resistance, junction to case	R_{thJC}	per diode			22.0	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}^*\text{K})$		14.4		K/kW
Temperature under switching conditions	T_{vjop}		-50		125	$^\circ\text{C}$

4 Characteristics diagrams

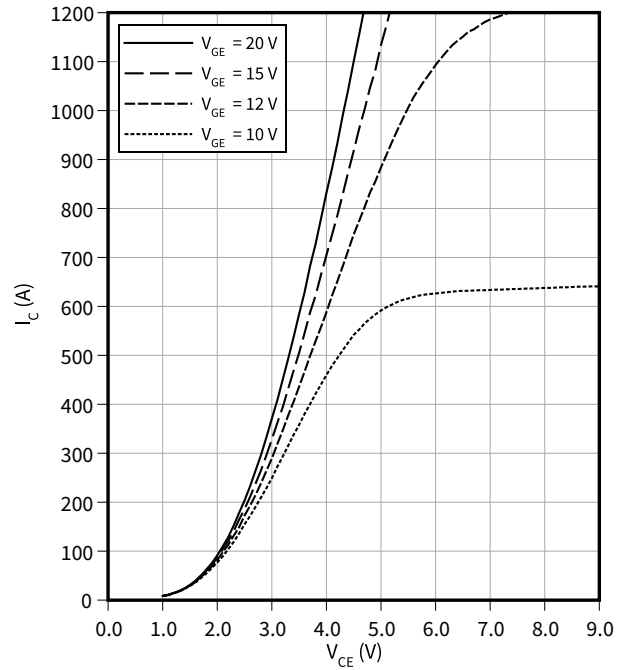
output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$
 $V_{GE} = 15 \text{ V}$



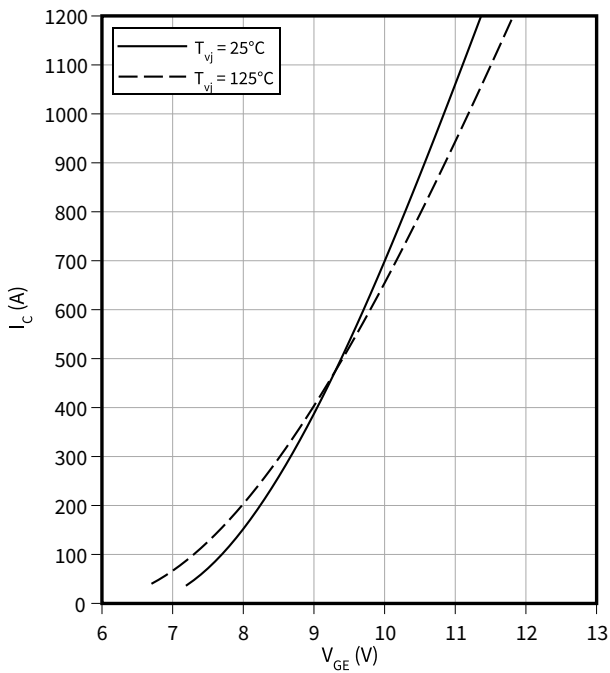
output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$
 $T_{vj} = 125 \text{ °C}$



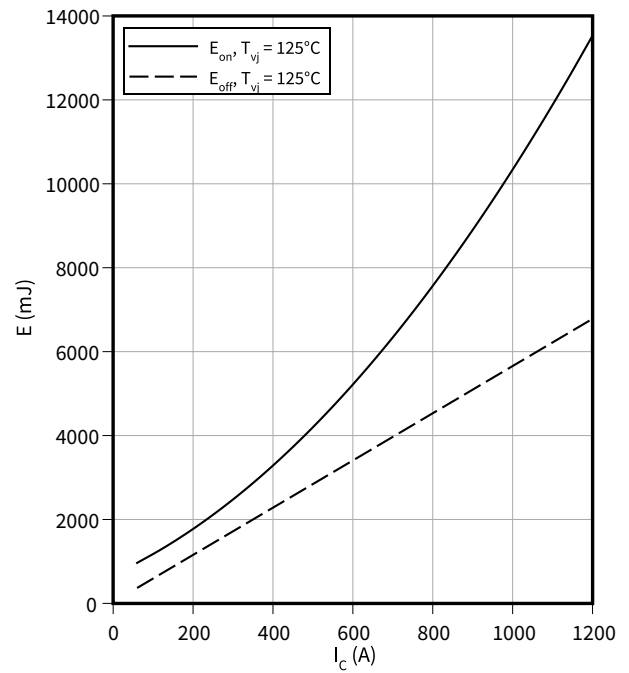
transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$
 $V_{CE} = 20 \text{ V}$



switching losses (typical), IGBT, Inverter

$E = f(I_C)$
 $R_{Goff} = 8.2 \text{ } \Omega$, $R_{Gon} = 1.3 \text{ } \Omega$, $V_{CE} = 3600 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$

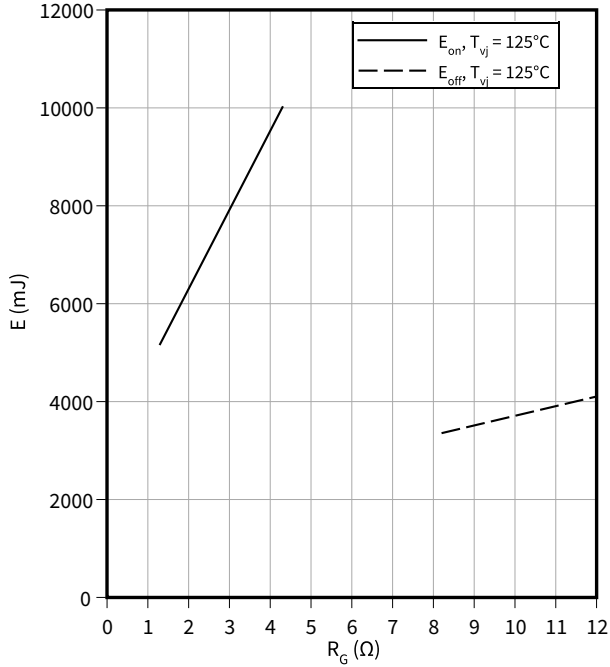


4 Characteristics diagrams

switching losses (typical), IGBT, Inverter

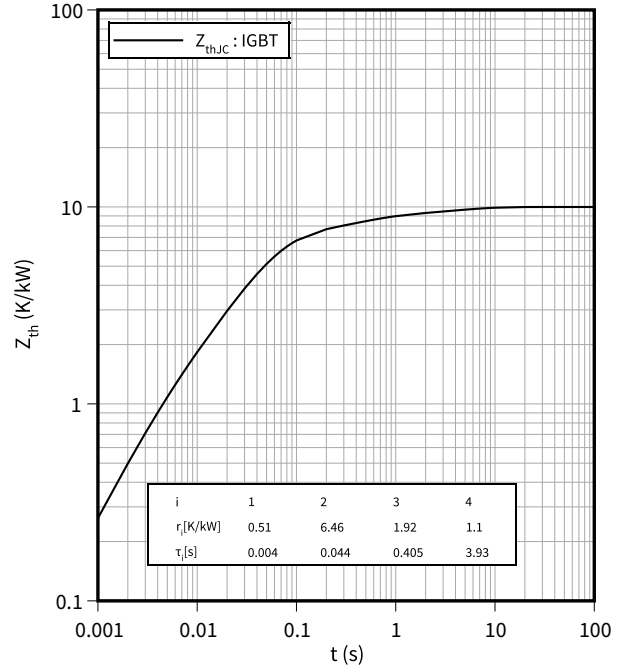
$E = f(R_G)$

$I_C = 600 \text{ A}$, $V_{CE} = 3600 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$



transient thermal impedance , IGBT, Inverter

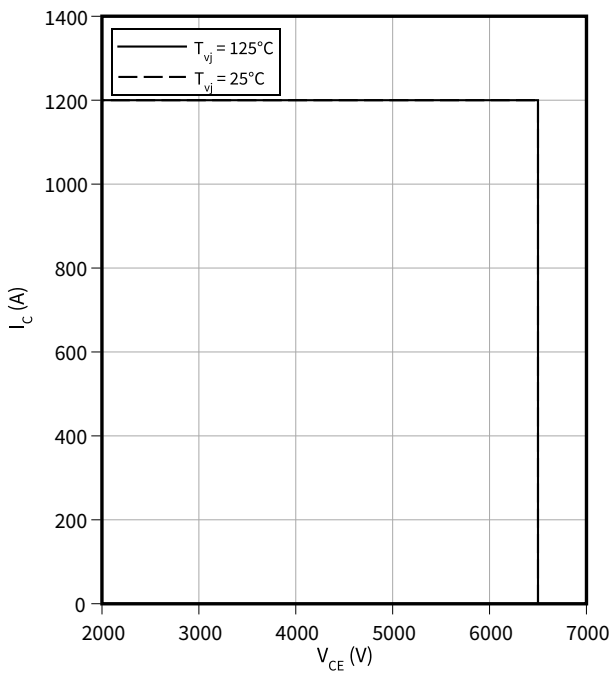
$Z_{th} = f(t)$



reverse bias safe operating area (RBSOA), IGBT, Inverter

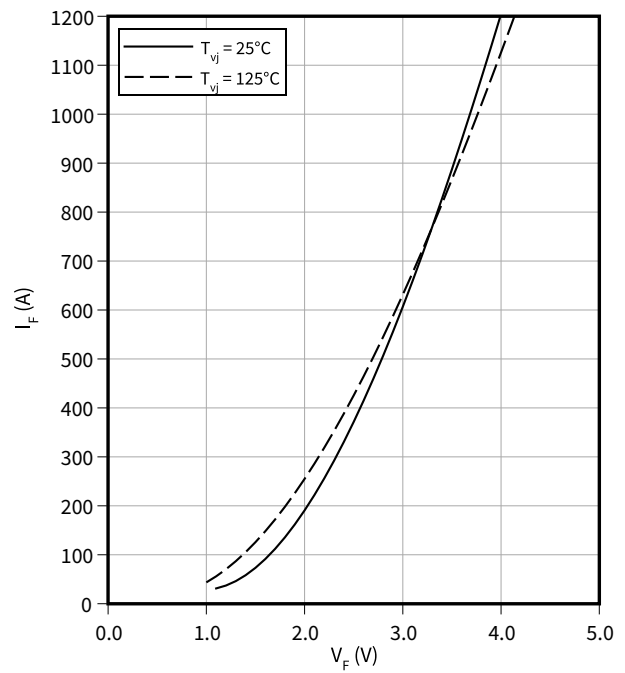
$I_C = f(V_{CE})$

$R_{Goff} = 8.2 \Omega$, $V_{GE} = \pm 15 \text{ V}$



forward characteristic of (typical), Diode, Inverter

$I_F = f(V_F)$

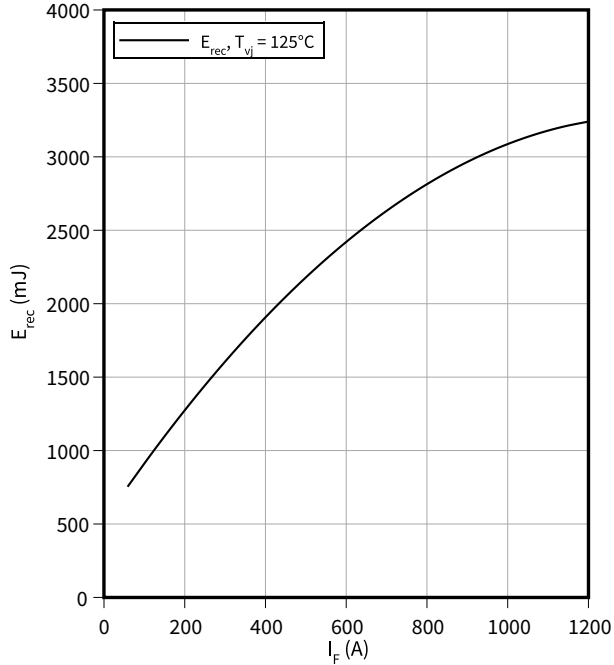


4 Characteristics diagrams

switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

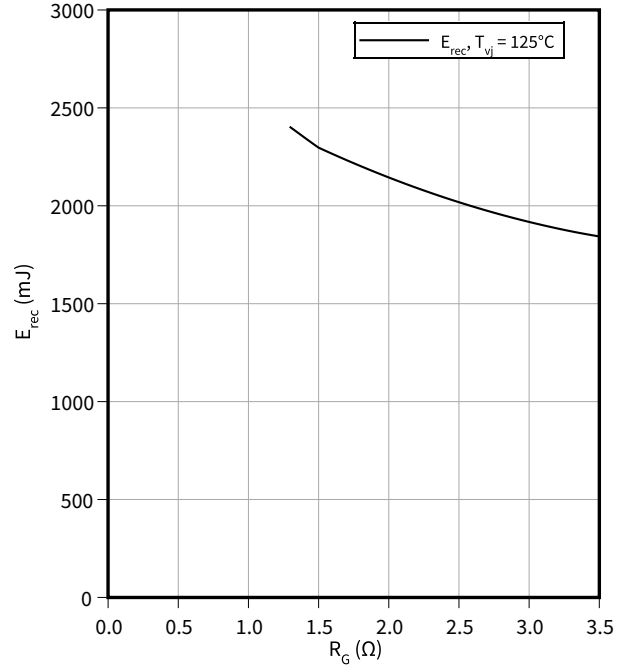
$V_{CE} = 3600\text{ V}, R_{Gon} = R_{Gon}(IGBT)$



switching losses (typical), Diode, Inverter

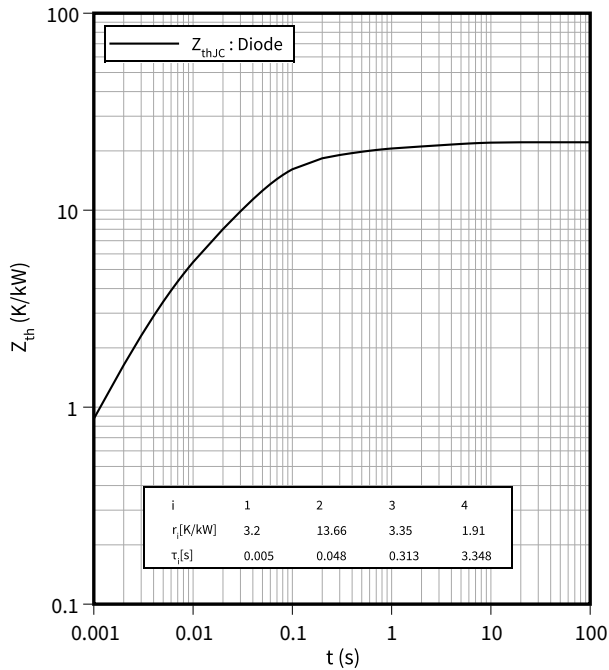
$E_{rec} = f(R_G)$

$V_{CE} = 3600\text{ V}, I_F = 600\text{ A}$



transient thermal impedance, Diode, Inverter

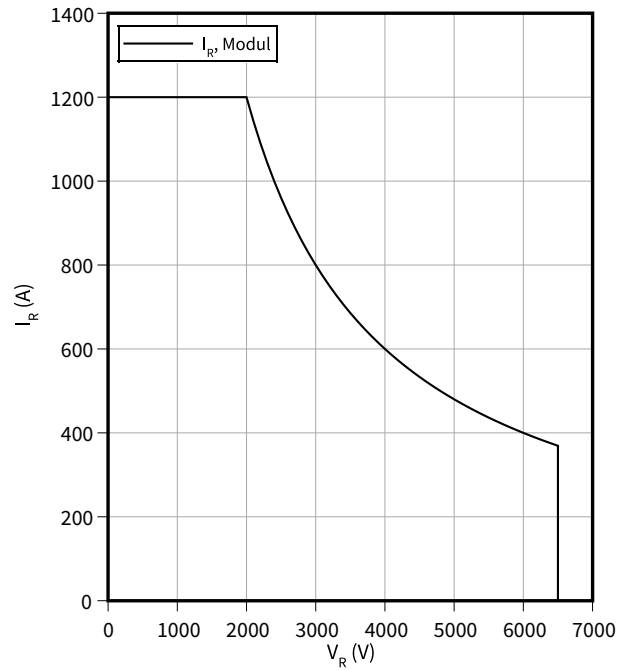
$Z_{th} = f(t)$



safe operation area (SOA), Diode, Inverter

$I_R = f(V_R)$

$T_{vj} = 125\text{ °C}$



5 Circuit diagram

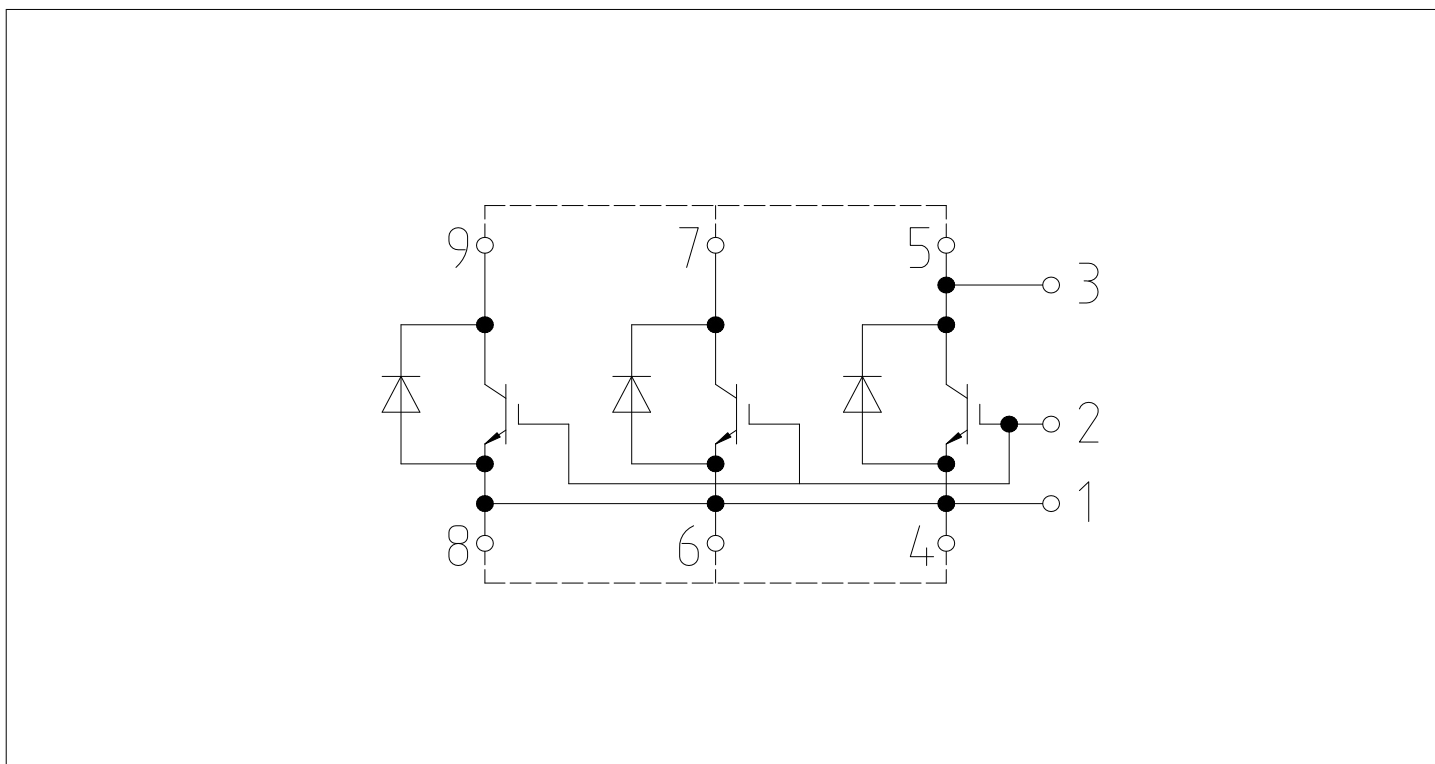


Figure 1

FZ600R65KE3
Highly insulated module



6 Package outlines

6 Package outlines

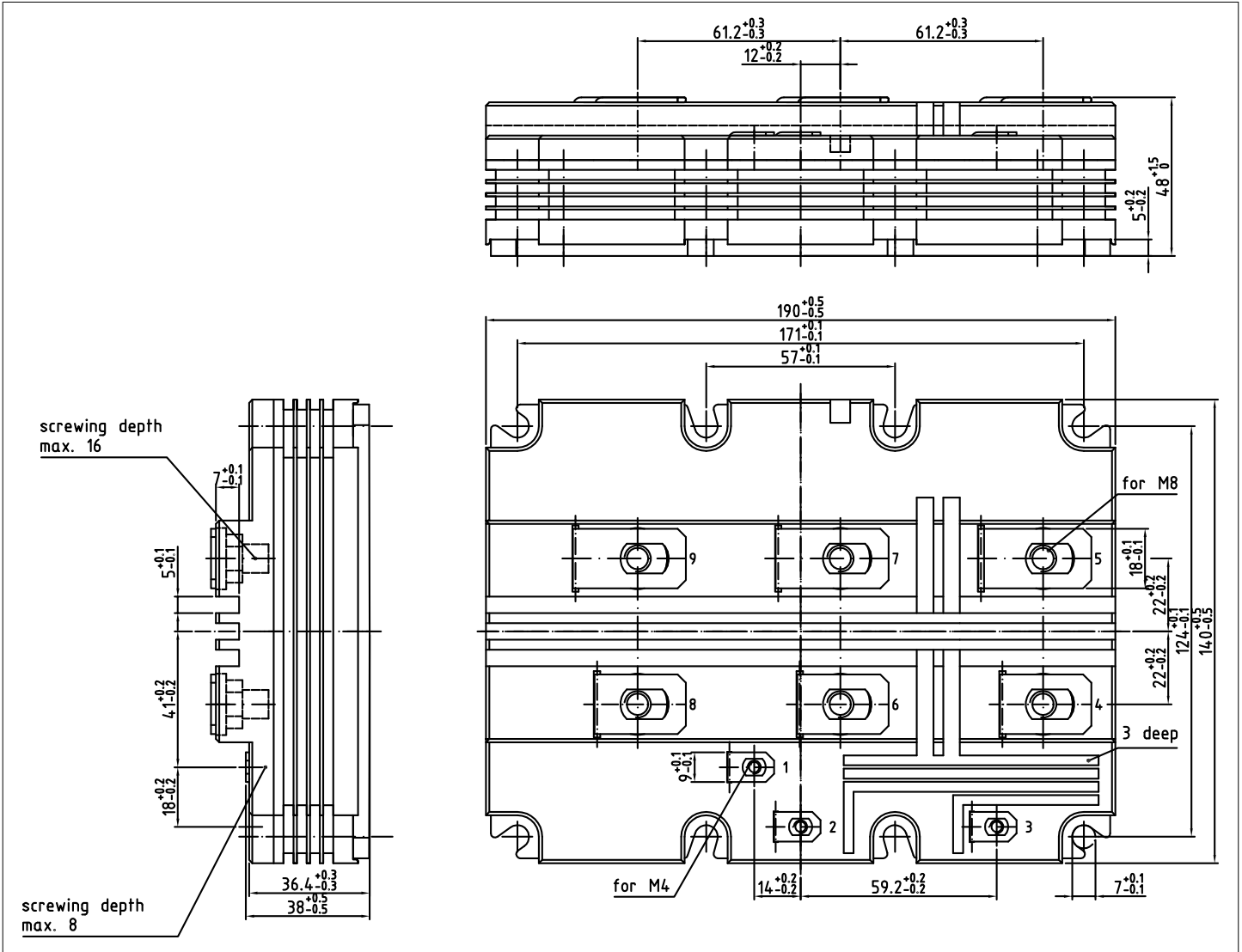


Figure 2

7 Module label code


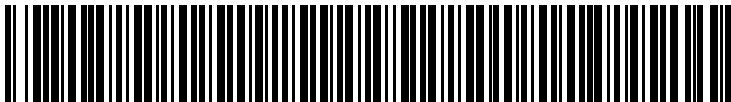
Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 - 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 - 21	15
	Date code (production week)	22 - 23	30
Example	 		
	71549142846550549911530		71549142846550549911530

Figure 3

Revision history

Document revision	Date of release	Description of changes
V1.0	2009-06-23	Target datasheet
V1.1	2010-01-14	Target datasheet
V2.0	2010-12-06	Preliminary datasheet
V2.1	2012-06-14	Preliminary datasheet
V2.2	2012-06-25	Preliminary datasheet
V2.3	2012-08-22	Preliminary datasheet
V3.0	2015-02-13	Final datasheet
V3.1	2016-08-30	Final datasheet
V3.2	2018-01-15	Final datasheet
V3.3	2019-09-06	Final datasheet
V3.4	2020-05-06	Final datasheet
n/a	2020-09-01	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.10	2021-10-29	Final datasheet

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